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Virtex UltraScale+ FPGA Data Sheet: DC and AC Switching Characteristics

DS923 (v1.1) April 19, 2017 **Preliminary Product Specification**

Summary

The Xilinx® Virtex® UltraScale+™ FPGAs are available in -3, -2, -1 speed grades, with -3E devices having the highest performance. The -2LE devices can operate at a V_{CCINT} voltage at 0.85V or 0.72V and provide lower maximum static power. When operated at V_{CCINT} = 0.85V, using -2LE devices, the speed specification for the L devices is the same as the -2I speed grade. When operated at V_{CCINT} = 0.72V, the -2LE performance and static and dynamic power is reduced.

DC and AC characteristics are specified in extended (E) and industrial (I) temperature ranges. Except the operating temperature range or unless otherwise noted, all the DC and AC electrical parameters are the same for a particular speed grade (that is, the timing characteristics of a -1 speed grade extended device are the same as for a -1 speed grade industrial device). However, only selected speed grades and/or devices are available in each temperature range.

All supply voltage and junction temperature specifications are representative of worst-case conditions. The parameters included are common to popular designs and typical applications.

This data sheet, part of an overall set of documentation on the Virtex UltraScale+ FPGAs, is available on the Xilinx website at www.xilinx.com/documentation.

DC Characteristics

Absolute Maximum Ratings

Table 1: **Absolute Maximum Ratings(1)**

Symbol	Description	Min	Max	Units
FPGA Logic				
V_{CCINT}	Internal supply voltage.	–0.500	1.000	V
V_{CCINT_IO}(2)	Internal supply voltage for the I/O banks.	–0.500	1.000	V
V_{CCAUX}	Auxiliary supply voltage.	–0.500	2.000	V
V_{CCBRAM}	Supply voltage for the block RAM memories.	–0.500	1.000	V
V_{CCO}	Output drivers supply voltage for the I/O banks.	–0.500	2.000	V
V_{CCAUX_IO}(3)	Auxiliary supply voltage for the I/O banks.	–0.500	2.000	V
V_{REF}	Input reference voltage.	–0.500	2.000	V
V_{IN}(4)(5)(6)	I/O input voltage for I/O banks.	–0.550	V_{CCO} + 0.550	V
V_{BATT}	Key memory battery backup supply	–0.500	2.000	V
I_{DC}	Available output current at the pad.	–20	20	mA

Table 1: **Absolute Maximum Ratings(1) *(Cont'd)***

Symbol	Description	Min	Max	Units
I_{RMS}	Available RMS output current at the pad.	–20	20	mA
GTY Transceivers				
$V_{MGTAVCC}$	Analog supply voltage for transceiver circuits.	–0.500	1.000	V
$V_{MGTAVTT}$	Analog supply voltage for transceiver termination circuits.	–0.500	1.300	V
$V_{MGTVCCAUX}$	Auxiliary analog Quad PLL (QPLL) voltage supply for transceivers.	–0.500	1.900	V
$V_{MGTREFCLK}$	Transceiver reference clock absolute input voltage.	–0.500	1.300	V
$V_{MGTAVTTRCAL}$	Analog supply voltage for the resistor calibration circuit of the transceiver column.	–0.500	1.300	V
V_{IN}	Receiver (RXP/RXN) and transmitter (TXP/TXN) absolute input voltage.	–0.500	1.200	V
$I_{DCIN-FLOAT}$	DC input current for receiver input pins DC coupled RX termination = floating.(7)	–	10	mA
$I_{DCIN-MGTAVTT}$	DC input current for receiver input pins DC coupled RX termination = $V_{MGTAVTT}$.	–	10	mA
$I_{DCIN-GND}$	DC input current for receiver input pins DC coupled RX termination = GND.(8)	–	0	mA
$I_{DCIN-PROG}$	DC input current for receiver input pins DC coupled RX termination = programmable.(9)	–	0	mA
$I_{DCOUT-FLOAT}$	DC output current for transmitter pins DC coupled RX termination = floating.	–	6	mA
$I_{DCOUT-MGTAVTT}$	DC output current for transmitter pins DC coupled RX termination = $V_{MGTAVTT}$.	–	6	mA
System Monitor				
V_{CCADC}	System Monitor supply relative to GNDADC.	0.500	2.000	V
V_{REFP}	System Monitor reference input relative to GNDADC.	0.500	2.000	V
Temperature				
T_{STG}	Storage temperature (ambient).	–65	150	°C
T_{SOL}	Maximum soldering temperature.(11)	–	260	°C
T_j	Maximum junction temperature.(11)	–	125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. V_{CCINT_IO} must be connected to V_{CCBRAM}.
3. V_{CCAUX_IO} must be connected to V_{CCAUX}.
4. The lower absolute voltage specification always applies.
5. For I/O operation, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
6. When operating outside of the recommended operating conditions, refer to Table 4 for maximum overshoot and undershoot specifications.
7. AC coupled operation is not supported for RX termination = floating.
8. For GTY transceivers, DC coupled operation is not supported for RX termination = GND.
9. DC coupled operation is not supported for RX termination = programmable.
10. For more information on supported GTY transceiver terminations see the or *UltraScale Architecture GTY Transceiver User Guide* (UG578)
11. For soldering guidelines and thermal considerations, see the *UltraScale and UltraScale+ FPGA Packaging and Pinout Specifications* (UG575).

Recommended Operating Conditions

Table 2: **Recommended Operating Conditions(1)(2)**

Symbol	Description	Min	Typ	Max	Units
FPGA Logic					
V_{CCINT}	Internal supply voltage.	0.825	0.850	0.876	V
	For -2LE (V_{CCINT} = 0.72V) devices: internal supply voltage.	0.698	0.720	0.742	V
	For -3E devices: internal supply voltage.	0.873	0.900	0.927	V
V_{CCINT_IO}(3)	Internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -2LE devices (V_{CCINT} = 0.85V): internal supply voltage for the I/O banks.	0.825	0.850	0.876	V
	For -3E devices: internal supply voltage for the I/O banks.	0.873	0.900	0.927	V
V_{CCBRAM}	Block RAM supply voltage.	0.825	0.850	0.876	V
	For -3E devices: block RAM supply voltage.	0.873	0.900	0.927	V
V_{CCAUX}	Auxiliary supply voltage.	1.746	1.800	1.854	V
V_{CCO}(4)(5)	Supply voltage for I/O banks.	0.950	–	1.900	V
V_{CCAUX_IO}(6)	Auxiliary I/O supply voltage.	1.746	1.800	1.854	V
V_{IN}(7)	I/O input voltage.	–0.200	–	V_{CCO} + 0.200	V
I_{IN}(8)	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	–	10	mA
V_{BATT}(9)	Battery voltage.	1.000	–	1.890	V
GTY Transceiver					
$V_{MGTAVCC}$(10)	Analog supply voltage for the GTY transceiver.	0.873	0.900	0.927	V
$V_{MGTAVTT}$(10)	Analog supply voltage for the GTY transmitter and receiver termination circuits.	1.164	1.20	1.236	V
$V_{MGTVCCAUX}$(10)	Auxiliary analog QPLL voltage supply for the transceivers.	1.746	1.80	1.854	V
$V_{MGTAVTTRCAL}$(10)	Analog supply voltage for the resistor calibration circuit of the GTY transceiver column.	1.164	1.20	1.236	V

Table 2: **Recommended Operating Conditions(1)(2) *(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
SYSMON					
V_{CCADC}	SYSMON supply relative to GNDADC.	1.746	1.800	1.854	V
V_{REFP}	SYSMON externally supplied reference voltage relative to GNDADC.	1.200	1.250	1.300	V
Temperature					
T_j(11)	Junction temperature operating range for extended (E) temperature devices.(12)	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices.	–40	–	100	°C
	Junction temperature operating range for eFUSE programming.(13)	–40	–	125	°C

Notes:

1. All voltages are relative to GND.
2. For the design of the power distribution system consult *UltraScale Architecture PCB Design Guide* (UG583).
3. V_{CCINT_IO} must be connected to V_{CCBRAM}.
4. For V_{CCO_0}, the minimum recommended operating voltage for power on and during configuration is 1.425V. After configuration, data is retained even if V_{CCO} drops to 0V.
5. Includes V_{CCO} of 1.0V, 1.2V, 1.35V, 1.5V, and 1.8V.
6. V_{CCAUX_IO} must be connected to V_{CCAUX}.
7. The lower absolute voltage specification always applies.
8. A total of 200 mA per bank should not be exceeded.
9. If battery is not used, connect V_{BATT} to either GND or V_{CCAUX}.
10. Each voltage listed requires filtering as described in the *UltraScale Architecture GTY Transceiver User Guide* (UG578).
11. Xilinx recommends measuring the Tj of a device using the system monitor as described in the *UltraScale Architecture System Monitor User Guide* (UG580). The SYSMON temperature measurement errors (that are described in Table 58) must be accounted for in your design. For example, by using an external reference of 1.25V, when SYSMON reports 97°C, there is a measurement error ±3°C. A reading of 97°C is considered the maximum adjusted Tj (100°C – 3°C = 97°C).
12. Devices labeled with the speed/temperature grade of -2LE can operate for a limited time at a junction temperature of 110°C. Timing parameters adhere to the same speed file at 110°C as they do below 110°C, regardless of operating voltage (nominal voltage of 0.85V or a low-voltage of 0.72V). Operation at Tj = 110°C is limited to 1% of the device lifetime and can occur sequentially or at regular intervals as long as the total time does not exceed 1% of the device lifetime.
13. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).

DC Characteristics Over Recommended Operating Conditions

Table 3: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ(1)	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.68	–	–	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested).(2)	–	–	15	µA
C_{IN}(3)	Die input capacitance at the pad.	–	–	3.1	pF
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 3.3V.	75	–	190	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 2.5V.	50	–	169	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.8V.	60	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.5V.	30	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.2V.	10	–	100	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	60	–	200	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	29	–	120	µA
$I_{CCADCON}$	Analog supply current for the SYSMON circuits in the power-up state.	–	–	8	mA
$I_{CCADCOFF}$	Analog supply current for the SYSMON circuits in the power-down state.	–	–	1.5	mA
I_{BATT}(4)(5)	Battery supply current at V_{BATT} = 1.89V.	–	–	650	nA
	Battery supply current at V_{BATT} = 1.20V.	–	–	150	nA
I_{PFS}(6)	V_{CCAUX} additional supply current during eFUSE programming.	–	–	115	mA
Calibrated programmable on-die termination (DCI) in I/O banks(8) (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_40.	–10%(8)	40	+10%(8)	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–10%(8)	48	+10%(8)	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_60.	–10%(8)	60	+10%(8)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–10%(8)	40	+10%(8)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–10%(8)	48	+10%(8)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–10%(8)	60	+10%(8)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–10%(8)	120	+10%(8)	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–10%(8)	240	+10%(8)	Ω

Table 3: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
Uncalibrated programmable on-die termination in I/O banks (measured per JEDEC specification)					
R(9)	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_40.	–50%	40	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_48.	–50%	48	+50%	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_40.	–50%	40	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_48.	–50%	48	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_60.	–50%	60	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_120.	–50%	120	+50%	Ω
	Programmable input termination to V_{CCO} where ODT = RTT_240.	–50%	240	+50%	Ω
Internal V_{REF}	50% V_{CCO}	V_{CCO} x 0.49	V_{CCO} x 0.50	V_{CCO} x 0.51	V
	70% V_{CCO}	V_{CCO} x 0.69	V_{CCO} x 0.70	V_{CCO} x 0.71	V
Differential termination	Programmable differential termination (TERM_100) for the I/O banks.	–35%	100	+35%	Ω
n	Temperature diode ideality factor.	–	1.026	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. For the I/O banks with a V_{CCO} of 1.8V and separated V_{CCO} and V_{CCAUX_IO} power supplies, the I_L maximum current is 70 µA.
3. This measurement represents the die capacitance at the pad, not including the package.
4. Maximum value specified for worst case process at 25°C.
5. I_{BATT} is measured when the battery-backed RAM (BBRAM) is enabled.
6. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).
7. If VRP resides at a different bank (DCI cascade), the range increases to ±15%.
8. VRP resistor tolerance is (240Ω ±1%)
9. On-die input termination resistance, for more information see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot

Table 4: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HP I/O Banks(1)(2)**

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO} + 0.30	100%	–0.30	100%
V_{CCO} + 0.35	100%	–0.35	90%
V_{CCO} + 0.40	92%	–0.40	92%
V_{CCO} + 0.45	50%	–0.45	50%
V_{CCO} + 0.50	20%	–0.50	20%
V_{CCO} + 0.55	10%	–0.55	10%
V_{CCO} + 0.60	6%	–0.60	6%
V_{CCO} + 0.65	2%	–0.65	2%
V_{CCO} + 0.70	2%	–0.70	2%

Notes:
1. A total of 200 mA per bank should not be exceeded.
2. For UI smaller than 20 µs.

Quiescent Supply Current

Table 5: **Typical Quiescent Supply Current(1)(2)(3)**

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages				Units
			0.90V	0.85V		0.72V	
			-3	-2	-1	-2	
I_{CCINTQ}	Quiescent V_{CCINT} supply current.	XCVU3P	2384	2276	2276	2017	mA
		XCVU5P	4769	4552	4552	4034	mA
		XCVU7P	4769	4552	4552	4034	mA
		XCVU9P	7153	6828	6828	6050	mA
		XCVU11P	7567	7202	7202	6332	mA
		XCVU13P	10090	9602	9602	8442	mA
I_{CCINT_IOQ}	Quiescent current for V_{CCINT_IO} supply.	XCVU3P	149	144	144	144	mA
		XCVU5P	298	287	287	287	mA
		XCVU7P	298	287	287	287	mA
		XCVU9P	447	431	431	431	mA
		XCVU11P	182	176	176	176	mA
		XCVU13P	243	234	234	234	mA
I_{CCOQ}	Quiescent V_{CCO} supply current.	All devices	1	1	1	1	mA
I_{CCAUXQ}	Quiescent V_{CCAUX} supply current.	XCVU3P	268	268	268	268	mA
		XCVU5P	535	535	535	535	mA
		XCVU7P	535	535	535	535	mA
		XCVU9P	1015	1015	1015	1015	mA
		XCVU11P	819	819	819	819	mA
		XCVU13P	1091	1091	1091	1091	mA

Table 5: **Typical Quiescent Supply Current(1)(2)(3) *(Cont'd)***

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages				Units
			0.90V	0.85V		0.72V	
			-3	-2	-1	-2	
I_{CCAUX_IOQ}	Quiescent V_{CCAUX_IO} supply current.	XCVU3P	62	62	62	62	mA
		XCVU5P	124	124	124	124	mA
		XCVU7P	124	124	124	124	mA
		XCVU9P	187	187	187	187	mA
		XCVU11P	79	79	79	79	mA
		XCVU13P	105	105	105	105	mA
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current.	XCVU3P	45	43	43	43	mA
		XCVU5P	90	85	85	85	mA
		XCVU7P	90	85	85	85	mA
		XCVU9P	134	128	128	128	mA
		XCVU11P	130	124	124	124	mA
		XCVU13P	174	165	165	165	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO™ resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCINT_IO}/V_{CCBRAM}, V_{CCAUX}/V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCINT_IO}/V_{CCBRAM} have the same recommended voltage levels, they can be powered by the same supply and ramped simultaneously. V_{CCINT_IO} must be connected to V_{CCBRAM}. If V_{CCAUX}/V_{CCAUX_IO} and V_{CCO} have the same recommended voltage levels, they can be powered by the same supply and ramped simultaneously. V_{CCAUX} and V_{CCAUX_IO} must be connected together. V_{CCADC} and V_{REF} can be powered at any time and have no power-up sequencing requirements.

The recommended power-on sequence to achieve minimum current draw for the GTY transceivers are V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

Power Supply Requirements

Table 6 shows the minimum current, in addition to I_{CCQ} maximum, required by each Virtex UltraScale+ FPGA for proper power-on and configuration. If the current minimums shown in Table 6 are met, the device powers on after all supplies have passed through their power-on reset threshold voltages. The device must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 6: **Power-on Current by Device(1)**

Device	$I_{CCINTMIN}$	$I_{CCINT\_IOMIN} + I_{CCBRAMMIN}$	I_{CCOMIN}	$I_{CCAUXMIN} + I_{CCAUX\_IOMIN}$	Units
XCVU3P	I_{CCINTQ} + 2000	$I_{CCBRAMQ} + I_{CCINT\_IOQ}$ + 950	I_{CCOQ} + 50	$I_{CCAUXQ} + I_{CCAUX\_IOQ}$ + 350	mA
XCVU5P	I_{CCINTQ} + 4000	$I_{CCBRAMQ} + I_{CCINT\_IOQ}$ + 1900	I_{CCOQ} + 100	$I_{CCAUXQ} + I_{CCAUX\_IOQ}$ + 700	mA
XCVU7P	I_{CCINTQ} + 4000	$I_{CCBRAMQ} + I_{CCINT\_IOQ}$ + 1900	I_{CCOQ} + 100	$I_{CCAUXQ} + I_{CCAUX\_IOQ}$ + 700	mA
XCVU9P	I_{CCINTQ} + 6000	$I_{CCBRAMQ} + I_{CCINT\_IOQ}$ + 2850	I_{CCOQ} + 150	$I_{CCAUXQ} + I_{CCAUX\_IOQ}$ + 1050	mA
XCVU11P	I_{CCINTQ} + 6549	$I_{CCBRAMQ} + I_{CCINT\_IOQ}$ + 3111	I_{CCOQ} + 164	$I_{CCAUXQ} + I_{CCAUX\_IOQ}$ + 1146	mA
XCVU13P	I_{CCINTQ} + 8731	$I_{CCBRAMQ} + I_{CCINT\_IOQ}$ + 4148	I_{CCOQ} + 219	$I_{CCAUXQ} + I_{CCAUX\_IOQ}$ + 1528	mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate power-on current for all supplies.

Table 7 shows the power supply ramp time.

Table 7: **Power Supply Ramp Time**

Symbol	Description	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 95% of V_{CCINT}.	0.2	40	ms
T_{VCCINT_IO}	Ramp time from GND to 95% of V_{CCINT_IO}.	0.2	40	ms
T_{VCCO}	Ramp time from GND to 95% of V_{CCO}.	0.2	40	ms
T_{VCCAUX}	Ramp time from GND to 95% of V_{CCAUX}.	0.2	40	ms
$T_{VCCBRAM}$	Ramp time from GND to 95% of V_{CCBRAM}.	0.2	40	ms
$T_{MGTAVCC}$	Ramp time from GND to 95% of $V_{MGTAVCC}$.	0.2	40	ms
$T_{MGTAVTT}$	Ramp time from GND to 95% of $V_{MGTAVTT}$.	0.2	40	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 95% of $V_{MGTVCCAUX}$.	0.2	40	ms

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 8: **SelectIO DC Input and Output Levels for the I/O Banks(1)(2)(3)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	5.8	–5.8
HSTL_I_12	–0.300	V_{REF} – 0.080	V_{REF} + 0.080	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	4.1	–4.1
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	6.2	–6.2
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVDCI_15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	7.0	–7.0
LVDCI_18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	7.0	–7.0
SSTL12	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	$V_{CCO}/2$ – 0.150	$V_{CCO}/2$ + 0.150	8.0	–8.0
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	$V_{CCO}/2$ – 0.150	$V_{CCO}/2$ + 0.150	9.0	–9.0
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	$V_{CCO}/2$ – 0.175	$V_{CCO}/2$ + 0.175	10.0	–10.0
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	$V_{CCO}/2$ – 0.470	$V_{CCO}/2$ + 0.470	7.0	–7.0
MIPI_DPHY_DCI_LP(6)	–0.300	0.550	0.880	V_{CCO} + 0.300	0.050	1.100	0.01	–0.01

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
3. POD10 and POD12 DC input and output levels are shown in Table 9, Table 13, and Table 14.
4. Supported drive strengths of 2, 4, 6, or 8 mA in the I/O banks.
5. Supported drive strengths of 2, 4, 6, 8, or 12 mA in the I/O banks.
6. Low-power option for MIPI_DPHY_DCI.

Table 9: **DC Input Levels for Single-ended POD10 and POD12 I/O Standards(1)(2)**

I/O Standard	V_{IL}		V_{IH}	
	V, Min	V, Max	V, Min	V, Max
POD10	–0.300	V_{REF} – 0.068	V_{REF} + 0.068	V_{CCO} + 0.300
POD12	–0.300	V_{REF} – 0.068	V_{REF} + 0.068	V_{CCO} + 0.300

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 10: **Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM} (V)(1)			V_{ID} (V)(2)			V_{ILHS}(3)	V_{IHHS}(3)	V_{OCM} (V)(4)			V_{OD} (V)(5)		
	Min	Typ	Max	Min	Typ	Max	Min	Max	Min	Typ	Max	Min	Typ	Max
SUB_LVDS	0.500	0.900	1.300	0.070	–	–	–	–	0.700	0.900	1.100	0.100	0.150	0.200
SLVS_400_18	0.070	0.200	0.330	0.140	–	0.450	–	–	–	–	–	–	–	–
MIPI_DPHY_DCI_HS(7)	0.070	–	0.330	0.070	–	–	–0.040	0.460	0.150	0.200	0.250	0.140	0.200	0.270

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage ($Q - \overline{Q}$).
3. V_{IHHS} and V_{ILHS} are the single-ended input high and low voltages, respectively.
4. V_{OCM} is the output common mode voltage.
5. V_{OD} is the output differential voltage ($Q - \overline{Q}$).
6. LVDS is specified in Table 15.
7. High-speed option for MIPI_DPHY_DCI. The V_{ID} maximum is aligned with the standard's specification. A higher V_{ID} is acceptable as long as the V_{IN} specification is also met.

Table 11: **Complementary Differential SelectIO DC Input and Output Levels for the I/O Banks(1)**

I/O Standard	V_{ICM} (V)(2)			V_{ID} (V)(3)		V_{OL} (V)(4)	V_{OH} (V)(5)	I_{OL}	I_{OH}
	Min	Typ	Max	Min	Max	Max	Min	mA	mA
DIFF_HSTL_I	0.680	$V_{CCO}/2$	$(V_{CCO}/2) + 0.150$	0.100	–	0.400	$V_{CCO} - 0.400$	5.8	–5.8
DIFF_HSTL_I_12	$0.400 \times V_{CCO}$	$V_{CCO}/2$	$0.600 \times V_{CCO}$	0.100	–	$0.250 \times V_{CCO}$	$0.750 \times V_{CCO}$	4.1	–4.1
DIFF_HSTL_I_18	$(V_{CCO}/2) - 0.175$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.175$	0.100	–	0.400	$V_{CCO} - 0.400$	6.2	–6.2
DIFF_HSUL_12	$(V_{CCO}/2) - 0.120$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.120$	0.100	–	$20\% V_{CCO}$	$80\% V_{CCO}$	0.1	–0.1
DIFF_SSTL12	$(V_{CCO}/2) - 0.150$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.150$	0.100	–	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	8.0	–8.0
DIFF_SSTL135	$(V_{CCO}/2) - 0.150$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.150$	0.100	–	$(V_{CCO}/2) - 0.150$	$(V_{CCO}/2) + 0.150$	9.0	–9.0
DIFF_SSTL15	$(V_{CCO}/2) - 0.175$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.175$	0.100	–	$(V_{CCO}/2) - 0.175$	$(V_{CCO}/2) + 0.175$	10.0	–10.0
DIFF_SSTL18_I	$(V_{CCO}/2) - 0.175$	$V_{CCO}/2$	$(V_{CCO}/2) + 0.175$	0.100	–	$(V_{CCO}/2) - 0.470$	$(V_{CCO}/2) + 0.470$	7.0	–7.0

Notes:

1. DIFF_POD10 and DIFF_POD12 HP I/O bank specifications are shown in Table 12, Table 13, and Table 14.
2. V_{ICM} is the input common mode voltage.
3. V_{ID} is the input differential voltage.
4. V_{OL} is the single-ended low-output voltage.
5. V_{OH} is the single-ended high-output voltage.

Table 12: **DC Input Levels for Differential POD10 and POD12 I/O Standards(1)(2)**

I/O Standard	V_{ICM} (V)			V_{ID} (V)	
	Min	Typ	Max	Min	Max
DIFF_POD10	0.63	0.70	0.77	0.14	–
DIFF_POD12	0.76	0.84	0.92	0.16	–

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 13: **DC Output Levels for Single-ended and Differential POD10 and POD12 Standards(1)(2)**

Symbol	Description	V_{OUT}	Min	Typ	Max	Units
R_{OL}	Pull-down resistance.	V_{OM_DC} (as described in Table 14)	36	40	44	Ω
R_{OH}	Pull-up resistance.	V_{OM_DC} (as described in Table 14)	36	40	44	Ω

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 14: **Table 13 Definitions for DC Output Levels for POD Standards**

Symbol	Description	All Speed Grades	Units
V_{OM_DC}	DC output Mid measurement level (for IV curve linearity).	0.8 x V_{CCO}	V

LVDS DC Specifications (LVDS)

Table 15: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}(1)	Supply voltage.		1.710	1.800	1.890	V
V_{ODIFF}(2)	Differential output voltage: ($\overline{Q}$ – Q), Q = High (Q – $\overline{Q}$), Q = High	R_T = 100Ω across Q and $\overline{Q}$ signals	247	350	454	mV
V_{OCM}(2)	Output common-mode voltage.	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential input voltage: ($\overline{Q}$ – Q), Q = High (Q – $\overline{Q}$), Q = High		100	350	600(3)	mV
V_{ICM_DC}(4)	Input common-mode voltage (DC coupling).		0.300	1.200	1.425	V
V_{ICM_AC}(5)	Input common-mode voltage (AC coupling).		0.600	–	1.100	V

Notes:

1. In I/O banks, when LVDS is used with input-only functionality, it can be placed in a bank where the V_{CCO} levels are different from the specified level only if internal differential termination is not used. In this scenario, V_{CCO} must be chosen to ensure the input pin voltage levels do not violate the *Recommended Operating Condition* (Table 2) specification for the V_{IN} I/O pin voltage.
2. V_{OCM} and V_{ODIFF} values are for LVDS_PRE_EMPHASIS = FALSE.
3. Maximum V_{IDIFF} value is specified for the maximum V_{ICM} specification. With a lower V_{ICM}, a higher V_{DIFF} is tolerated only when the recommended operating conditions and overshoot/undershoot V_{IN} specifications are maintained.
4. Input common mode voltage for DC coupled configurations. EQUALIZATION = EQ_NONE (Default).
5. External input common mode voltage specification for AC coupled configurations. EQUALIZATION = EQ_LEVEL0, EQ_LEVEL1, EQ_LEVEL2, EQ_LEVEL3, EQ_LEVEL4.

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications in the Vivado® Design Suite as outlined in Table 16.

Table 16: **Speed Specification Version By Device**

2017.1	Device
1.10	XCVU3P, XCVU7P, XCVU9P, XCVU5P, XCVU11P, XCVU13P

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Virtex UltraScale+ FPGAs.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. Table 16 correlates the current status of the Virtex UltraScale+ FPGA on a per speed grade basis.

Table 17: **Speed Grade Designations by Device**

Device	Speed Grade, Temperature Ranges, and V_{CCINT} Operating Voltages		
	Advance	Preliminary	Production
XCVU3P	-3E (V_{CCINT} = 0.90V) -2LE (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V)(1)		-2I (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V) -1I (V_{CCINT} = 0.85V)
XCVU5P	-3E (V_{CCINT} = 0.90V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V)(1)		
XCVU7P	-3E (V_{CCINT} = 0.90V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V)(1)		
XCVU9P	-3E (V_{CCINT} = 0.90V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V)(1)		
XCVU11P	-3E (V_{CCINT} = 0.90V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.72V)(1)		
XCVU13P	-3E (V_{CCINT} = 0.90V) -2I (V_{CCINT} = 0.85V), -2LE (V_{CCINT} = 0.85V) -1E (V_{CCINT} = 0.85V), -1I (V_{CCINT} = 0.85V) -2LE (V_{CCINT} = 0.72V)(1)		

Notes:

1. The lowest power -2L devices, where V_{CCINT} = 0.72V, are listed in the Vivado Design Suite as -2LV.

Production Silicon and Software Status

In some cases, a particular family member (and speed grade) is released to production before a speed specification is released with the correct label (Advance, Preliminary, Production). Any labeling discrepancies are corrected in subsequent speed specification releases.

Table 18 lists the production released Virtex UltraScale+ FPGA, speed grade, and the minimum corresponding supported speed specification version and Vivado software revisions. The Vivado software and speed specifications listed are the minimum releases required for production. All subsequent releases of software and speed specifications are valid.

Table 18: **Virtex UltraScale+ FPGA Device Production Software and Speed Specification Release**

Device	Speed Grade and V_{CCINT} Operating Voltages				
	0.90V	0.85V			0.72V
	-3	-2	-1	-2L	-2L
XCVU3P		Vivado tools 2017.1 v1.10			
XCVU5P					
XCVU7P					
XCVU9P					
XCVU11P					
XCVU13P					

Notes:

1. Blank entries indicate a device and/or speed grade in Advance or Preliminary status.

FPGA Logic Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Virtex UltraScale+ FPGAs. These values are subject to the same guidelines as the AC Switching Characteristics, page 13.

Table 19: **LVDS Component Mode Performance**

Description	Speed Grade and V_{CCINT} Operating Voltages								Units
	0.90V		0.85V				0.72V		
	-3		-2		-1		-2		
	Min	Max	Min	Max	Min	Max	Min	Max	
LVDS TX DDR (OSERDES 4:1, 8:1)	0	1250	0	1250	0	1250	0	1250	Mb/s
LVDS TX SDR (OSERDES 2:1, 4:1)	0	625	0	625	0	625	0	625	Mb/s
LVDS RX DDR (ISERDES 1:4, 1:8)(1)	0	1250	0	1250	0	1250	0	1250	Mb/s
LVDS RX SDR (ISERDES 1:2, 1:4)(1)	0	625	0	625	0	625	0	625	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications to achieve maximum performance. Package skews are not included and should be removed through PCB routing.

Table 20: **LVDS Native Mode Performance(1)(2)**

Description	DATA_WIDTH	Speed Grade and V_{CCINT} Operating Voltages								Units
		0.90V		0.85V				0.72V		
		-3		-2		-1		-2		
		Min	Max	Min	Max	Min	Max	Min	Max	
LVDS TX DDR (TX_BITSLICE)	4	375	1600	375	1600	375	1260	375	1400	Mb/s
	8	375	1600	375	1600	375	1260	375	1600	Mb/s
LVDS TX SDR (TX_BITSLICE)	4	187.5	800	187.5	800	187.5	630	187.5	700	Mb/s
	8	187.5	800	187.5	800	187.5	630	187.5	800	Mb/s
LVDS RX DDR (RX_BITSLICE)(3)	4	375	1600	375	1600	375	1260	375	1400	Mb/s
	8	375	1600	375	1600	375	1260	375	1600	Mb/s
LVDS RX SDR (RX_BITSLICE)(3)	4	187.5	800	187.5	800	187.5	630	187.5	700	Mb/s
	8	187.5	800	187.5	800	187.5	630	187.5	800	Mb/s

Notes:

1. Native mode is supported through the High-Speed SelectIO Interface Wizard available with the Vivado Design Suite.
2. PLL settings can restrict the minimum allowable data rate. For example, when using the PLL with CLKOUTPHY_MODE = VCO_HALF the minimum frequency is PLL_FVCOMIN/2.
3. LVDS receivers are typically bounded with certain applications to achieve maximum performance. Package skews are not included and should be removed through PCB routing.

Table 21: **MIPI D-PHY Performance**

Description	Speed Grade and V_{CCINT} Operating Voltages				Units
	0.90V	0.85V		0.72V	
	-3	-2	-1	-2	
MIPI D-PHY transmitter or receiver.	1500	1500	1260	1260	Mb/s

Table 22: **LVDS Native-Mode 1000BASE-X Support(1)**

Description	Speed Grade and V_{CCINT} Operating Voltages			
	0.90V	0.85V		0.72V
	-3	-2	-1	-2
1000BASE-X	Yes			

Notes:
1. 1000BASE-X support is based on the *IEEE Standard for CSMA/CD Access Method and Physical Layer Specifications* (IEEE Std 802.3-2008).

Table 23 provides the maximum data rates for applicable memory standards using the Virtex UltraScale+ FPGA memory PHY. Refer to Memory Interfaces for the complete list of memory interface standards supported and detailed specifications. The final performance of the memory interface is determined through a complete design implemented in the Vivado Design Suite, following guidelines in the *UltraScale Architecture PCB Design Guide* (UG583), electrical analysis, and characterization of the system.

Table 23: **Maximum Physical Interface (PHY) Rate for Memory Interfaces**

Memory Standard	DRAM Type	Speed Grade and V_{CCINT} Operating Voltages				Units
		0.90V	0.85V		0.72V	
		-3	-2	-1	-2	
DDR4	Single rank component	2666	2666	2400	2400	Mb/s
	1 rank DIMM(1)(2)	2400	2400	2133	2133	Mb/s
	2 rank DIMM(1)(3)	2133	2133	1866	1866	Mb/s
	4 rank DIMM(1)(4)	1600	1600	1333	1333	Mb/s
DDR3	Single rank component	2133	2133	2133	2133	Mb/s
	1 rank DIMM(1)(2)	1866	1866	1866	1866	Mb/s
	2 rank DIMM(1)(3)	1600	1600	1600	1600	Mb/s
	4 rank DIMM(1)(4)	1066	1066	1066	1066	Mb/s
DDR3L	Single rank component	1866	1866	1866	1866	Mb/s
	1 rank DIMM(1)(2)	1600	1600	1600	1600	Mb/s
	2 rank DIMM(1)(3)	1333	1333	1333	1333	Mb/s
	4 rank DIMM(1)(4)	800	800	800	800	Mb/s
QDR II+	Single rank component(5)	633	633	600	600	MHz
RLDRAM 3	Single rank component	1200	1200	1066	1066	MHz
QDR IV XP	Single rank component	1066	1066	1066	933	MHz
LPDDR3	Single rank component	1600	1600	1600	1600	Mb/s

Notes:
1. Dual in-line memory module (DIMM) includes RDIMM, SODIMM, UDIMM, and LRDIMM.
2. Includes: 1 rank 1 slot, DDP 2 rank, LRDIMM 2 or 4 rank 1 slot.
3. Includes: 2 rank 1 slot, 1 rank 2 slot, LRDIMM 2 rank 2 slot.
4. Includes: 2 rank 2 slot, 4 rank 1 slot.
5. The QDRII+ performance specifications are for burst-length 4 (BL = 4) implementations.

FPGA Logic Switching Characteristics

Table 24, high-performance IOB (HP), summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- $T_{INBUF\_DELAY\_PAD\_I}$ is the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- $T_{OUTBUF\_DELAY\_O\_PAD}$ is the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- $T_{OUTBUF\_DELAY\_TD\_PAD}$ is the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than $T_{OUTBUF\_DELAY\_TD\_PAD}$ when the DCITERMDISABLE pin is used.

IOB High Performance (HP) Switching Characteristics

Table 24: **IOB High Performance (HP) Switching Characteristics**

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$				$T_{OUTBUF\_DELAY\_O\_PAD}$				$T_{OUTBUF\_DELAY\_TD\_PAD}$				Units
	0.90V	0.85V		0.72V	0.90V	0.85V		0.72V	0.90V	0.85V		0.72V	
	-3	-2	-1	-2	-3	-2	-1	-2	-3	-2	-1	-2	
DIFF_HSTL_I_12_F	0.394	0.394	0.402	0.394	0.423	0.423	0.443	0.423	0.553	0.553	0.582	0.553	ns
DIFF_HSTL_I_12_M	0.394	0.394	0.402	0.394	0.552	0.552	0.583	0.552	0.641	0.641	0.679	0.641	ns
DIFF_HSTL_I_12_S	0.394	0.394	0.402	0.394	0.752	0.752	0.800	0.752	0.813	0.813	0.868	0.813	ns
DIFF_HSTL_I_18_F	0.319	0.319	0.339	0.319	0.456	0.456	0.474	0.456	0.576	0.576	0.606	0.576	ns
DIFF_HSTL_I_18_M	0.319	0.319	0.339	0.319	0.570	0.570	0.603	0.570	0.653	0.653	0.692	0.653	ns
DIFF_HSTL_I_18_S	0.319	0.319	0.339	0.319	0.782	0.782	0.834	0.782	0.816	0.816	0.871	0.816	ns
DIFF_HSTL_I_DCI_12_F	0.394	0.394	0.402	0.394	0.406	0.406	0.429	0.406	0.534	0.534	0.564	0.534	ns
DIFF_HSTL_I_DCI_12_M	0.394	0.394	0.402	0.394	0.557	0.557	0.587	0.557	0.653	0.653	0.694	0.653	ns
DIFF_HSTL_I_DCI_12_S	0.394	0.394	0.402	0.394	0.755	0.755	0.806	0.755	0.842	0.842	0.907	0.842	ns
DIFF_HSTL_I_DCI_18_F	0.323	0.323	0.339	0.323	0.445	0.445	0.461	0.445	0.566	0.566	0.595	0.566	ns
DIFF_HSTL_I_DCI_18_M	0.323	0.323	0.339	0.323	0.555	0.555	0.586	0.555	0.643	0.643	0.684	0.643	ns
DIFF_HSTL_I_DCI_18_S	0.323	0.323	0.339	0.323	0.762	0.762	0.818	0.762	0.836	0.836	0.900	0.836	ns
DIFF_HSTL_I_DCI_F	0.397	0.397	0.417	0.397	0.431	0.431	0.445	0.431	0.555	0.555	0.575	0.555	ns
DIFF_HSTL_I_DCI_M	0.397	0.397	0.417	0.397	0.553	0.553	0.583	0.553	0.644	0.644	0.684	0.644	ns
DIFF_HSTL_I_DCI_S	0.397	0.397	0.417	0.397	0.767	0.767	0.823	0.767	0.848	0.848	0.912	0.848	ns
DIFF_HSTL_I_F	0.404	0.404	0.417	0.404	0.423	0.423	0.443	0.423	0.549	0.549	0.581	0.549	ns
DIFF_HSTL_I_M	0.404	0.404	0.417	0.404	0.555	0.555	0.586	0.555	0.640	0.640	0.677	0.640	ns
DIFF_HSTL_I_S	0.404	0.404	0.417	0.404	0.767	0.767	0.818	0.767	0.811	0.811	0.866	0.811	ns
DIFF_HSUL_12_DCI_F	0.381	0.381	0.400	0.381	0.425	0.425	0.443	0.425	0.558	0.558	0.586	0.558	ns
DIFF_HSUL_12_DCI_M	0.381	0.381	0.400	0.381	0.557	0.557	0.587	0.557	0.653	0.653	0.694	0.653	ns
DIFF_HSUL_12_DCI_S	0.381	0.381	0.400	0.381	0.737	0.737	0.787	0.737	0.822	0.822	0.885	0.822	ns
DIFF_HSUL_12_F	0.394	0.394	0.402	0.394	0.412	0.412	0.430	0.412	0.538	0.538	0.566	0.538	ns
DIFF_HSUL_12_M	0.394	0.394	0.402	0.394	0.552	0.552	0.583	0.552	0.641	0.641	0.679	0.641	ns
DIFF_HSUL_12_S	0.394	0.394	0.402	0.394	0.752	0.752	0.800	0.752	0.813	0.813	0.868	0.813	ns

Table 24: **IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$				$T_{OUTBUF\_DELAY\_O\_PAD}$				$T_{OUTBUF\_DELAY\_TD\_PAD}$				Units
	0.90V	0.85V		0.72V	0.90V	0.85V		0.72V	0.90V	0.85V		0.72V	
	-3	-2	-1	-2	-3	-2	-1	-2	-3	-2	-1	-2	
DIFF_POD10_DCI_F	0.411	0.411	0.430	0.411	0.425	0.425	0.444	0.425	0.555	0.555	0.584	0.555	ns
DIFF_POD10_DCI_M	0.411	0.411	0.430	0.411	0.542	0.542	0.571	0.542	0.640	0.640	0.681	0.640	ns
DIFF_POD10_DCI_S	0.411	0.411	0.430	0.411	0.754	0.754	0.815	0.754	0.850	0.850	0.917	0.850	ns
DIFF_POD10_F	0.411	0.411	0.433	0.411	0.438	0.438	0.459	0.438	0.569	0.569	0.601	0.569	ns
DIFF_POD10_M	0.411	0.411	0.433	0.411	0.538	0.538	0.568	0.538	0.630	0.630	0.667	0.630	ns
DIFF_POD10_S	0.411	0.411	0.433	0.411	0.766	0.766	0.821	0.766	0.836	0.836	0.894	0.836	ns
DIFF_POD12_DCI_F	0.407	0.407	0.432	0.407	0.425	0.425	0.443	0.425	0.558	0.558	0.586	0.558	ns
DIFF_POD12_DCI_M	0.407	0.407	0.432	0.407	0.543	0.543	0.572	0.543	0.638	0.638	0.678	0.638	ns
DIFF_POD12_DCI_S	0.407	0.407	0.432	0.407	0.772	0.772	0.822	0.772	0.862	0.862	0.929	0.862	ns
DIFF_POD12_F	0.409	0.409	0.430	0.409	0.455	0.455	0.476	0.455	0.595	0.595	0.626	0.595	ns
DIFF_POD12_M	0.409	0.409	0.430	0.409	0.551	0.551	0.582	0.551	0.641	0.641	0.679	0.641	ns
DIFF_POD12_S	0.409	0.409	0.430	0.409	0.767	0.767	0.817	0.767	0.832	0.832	0.889	0.832	ns
DIFF_SSTL12_DCI_F	0.381	0.381	0.400	0.381	0.425	0.425	0.443	0.425	0.558	0.558	0.586	0.558	ns
DIFF_SSTL12_DCI_M	0.381	0.381	0.400	0.381	0.557	0.557	0.587	0.557	0.654	0.654	0.694	0.654	ns
DIFF_SSTL12_DCI_S	0.381	0.381	0.400	0.381	0.754	0.754	0.803	0.754	0.842	0.842	0.908	0.842	ns
DIFF_SSTL12_F	0.394	0.394	0.402	0.394	0.412	0.412	0.430	0.412	0.538	0.538	0.566	0.538	ns
DIFF_SSTL12_M	0.394	0.394	0.402	0.394	0.553	0.553	0.584	0.553	0.641	0.641	0.676	0.641	ns
DIFF_SSTL12_S	0.394	0.394	0.402	0.394	0.758	0.758	0.808	0.758	0.823	0.823	0.879	0.823	ns
DIFF_SSTL135_DCI_F	0.371	0.371	0.402	0.371	0.411	0.411	0.428	0.411	0.537	0.537	0.565	0.537	ns
DIFF_SSTL135_DCI_M	0.371	0.371	0.402	0.371	0.551	0.551	0.582	0.551	0.645	0.645	0.685	0.645	ns
DIFF_SSTL135_DCI_S	0.371	0.371	0.402	0.371	0.746	0.746	0.799	0.746	0.829	0.829	0.893	0.829	ns
DIFF_SSTL135_F	0.375	0.375	0.402	0.375	0.408	0.408	0.428	0.408	0.528	0.528	0.561	0.528	ns
DIFF_SSTL135_M	0.375	0.375	0.402	0.375	0.555	0.555	0.585	0.555	0.641	0.641	0.679	0.641	ns
DIFF_SSTL135_S	0.375	0.375	0.402	0.375	0.772	0.772	0.823	0.772	0.827	0.827	0.878	0.827	ns
DIFF_SSTL15_DCI_F	0.397	0.397	0.417	0.397	0.412	0.412	0.429	0.412	0.531	0.531	0.563	0.531	ns
DIFF_SSTL15_DCI_M	0.397	0.397	0.417	0.397	0.553	0.553	0.583	0.553	0.645	0.645	0.685	0.645	ns
DIFF_SSTL15_DCI_S	0.397	0.397	0.417	0.397	0.768	0.768	0.822	0.768	0.847	0.847	0.912	0.847	ns
DIFF_SSTL15_F	0.404	0.404	0.417	0.404	0.424	0.424	0.445	0.424	0.551	0.551	0.577	0.551	ns
DIFF_SSTL15_M	0.404	0.404	0.417	0.404	0.554	0.554	0.585	0.554	0.639	0.639	0.677	0.639	ns
DIFF_SSTL15_S	0.404	0.404	0.417	0.404	0.767	0.767	0.817	0.767	0.813	0.813	0.867	0.813	ns
DIFF_SSTL18_I_DCI_F	0.320	0.320	0.336	0.320	0.445	0.445	0.461	0.445	0.566	0.566	0.595	0.566	ns
DIFF_SSTL18_I_DCI_M	0.320	0.320	0.336	0.320	0.554	0.554	0.585	0.554	0.644	0.644	0.683	0.644	ns
DIFF_SSTL18_I_DCI_S	0.320	0.320	0.336	0.320	0.762	0.762	0.818	0.762	0.837	0.837	0.899	0.837	ns
DIFF_SSTL18_I_F	0.316	0.316	0.336	0.316	0.454	0.454	0.476	0.454	0.578	0.578	0.608	0.578	ns
DIFF_SSTL18_I_M	0.316	0.316	0.336	0.316	0.571	0.571	0.603	0.571	0.652	0.652	0.692	0.652	ns
DIFF_SSTL18_I_S	0.316	0.316	0.336	0.316	0.782	0.782	0.835	0.782	0.816	0.816	0.870	0.816	ns
HSLVDCI_15_F	0.393	0.393	0.415	0.393	0.425	0.425	0.443	0.425	0.548	0.548	0.579	0.548	ns
HSLVDCI_15_M	0.393	0.393	0.415	0.393	0.552	0.552	0.581	0.552	0.644	0.644	0.684	0.644	ns
HSLVDCI_15_S	0.393	0.393	0.415	0.393	0.748	0.748	0.802	0.748	0.827	0.827	0.890	0.827	ns
HSLVDCI_18_F	0.424	0.424	0.447	0.424	0.445	0.445	0.461	0.445	0.566	0.566	0.595	0.566	ns
HSLVDCI_18_M	0.424	0.424	0.447	0.424	0.567	0.567	0.598	0.567	0.658	0.658	0.699	0.658	ns

Table 24: **IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$				$T_{OUTBUF\_DELAY\_O\_PAD}$				$T_{OUTBUF\_DELAY\_TD\_PAD}$				Units
	0.90V	0.85V		0.72V	0.90V	0.85V		0.72V	0.90V	0.85V		0.72V	
	-3	-2	-1	-2	-3	-2	-1	-2	-3	-2	-1	-2	
HSLVDCI_18_S	0.424	0.424	0.447	0.424	0.761	0.761	0.817	0.761	0.836	0.836	0.900	0.836	ns
HSTL_I_12_F	0.378	0.378	0.399	0.378	0.423	0.423	0.443	0.423	0.553	0.553	0.582	0.553	ns
HSTL_I_12_M	0.378	0.378	0.399	0.378	0.551	0.551	0.582	0.551	0.642	0.642	0.679	0.642	ns
HSTL_I_12_S	0.378	0.378	0.399	0.378	0.750	0.750	0.799	0.750	0.813	0.813	0.868	0.813	ns
HSTL_I_18_F	0.322	0.322	0.339	0.322	0.456	0.456	0.474	0.456	0.576	0.576	0.606	0.576	ns
HSTL_I_18_M	0.322	0.322	0.339	0.322	0.569	0.569	0.602	0.569	0.653	0.653	0.692	0.653	ns
HSTL_I_18_S	0.322	0.322	0.339	0.322	0.781	0.781	0.833	0.781	0.816	0.816	0.871	0.816	ns
HSTL_I_DCI_12_F	0.378	0.378	0.399	0.378	0.406	0.406	0.429	0.406	0.534	0.534	0.564	0.534	ns
HSTL_I_DCI_12_M	0.378	0.378	0.399	0.378	0.556	0.556	0.586	0.556	0.654	0.654	0.694	0.654	ns
HSTL_I_DCI_12_S	0.378	0.378	0.399	0.378	0.754	0.754	0.803	0.754	0.842	0.842	0.907	0.842	ns
HSTL_I_DCI_18_F	0.321	0.321	0.339	0.321	0.445	0.445	0.461	0.445	0.566	0.566	0.595	0.566	ns
HSTL_I_DCI_18_M	0.321	0.321	0.339	0.321	0.554	0.554	0.585	0.554	0.643	0.643	0.684	0.643	ns
HSTL_I_DCI_18_S	0.321	0.321	0.339	0.321	0.761	0.761	0.817	0.761	0.836	0.836	0.900	0.836	ns
HSTL_I_DCI_F	0.393	0.393	0.415	0.393	0.431	0.431	0.445	0.431	0.555	0.555	0.575	0.555	ns
HSTL_I_DCI_M	0.393	0.393	0.415	0.393	0.552	0.552	0.581	0.552	0.644	0.644	0.684	0.644	ns
HSTL_I_DCI_S	0.393	0.393	0.415	0.393	0.766	0.766	0.821	0.766	0.847	0.847	0.912	0.847	ns
HSTL_I_F	0.378	0.378	0.399	0.378	0.423	0.423	0.443	0.423	0.549	0.549	0.581	0.549	ns
HSTL_I_M	0.378	0.378	0.399	0.378	0.554	0.554	0.585	0.554	0.640	0.640	0.677	0.640	ns
HSTL_I_S	0.378	0.378	0.399	0.378	0.766	0.766	0.816	0.766	0.811	0.811	0.866	0.811	ns
HSUL_12_DCI_F	0.378	0.378	0.399	0.378	0.425	0.425	0.443	0.425	0.558	0.558	0.586	0.558	ns
HSUL_12_DCI_M	0.378	0.378	0.399	0.378	0.556	0.556	0.586	0.556	0.654	0.654	0.694	0.654	ns
HSUL_12_DCI_S	0.378	0.378	0.399	0.378	0.736	0.736	0.784	0.736	0.821	0.821	0.886	0.821	ns
HSUL_12_F	0.378	0.378	0.399	0.378	0.412	0.412	0.430	0.412	0.538	0.538	0.566	0.538	ns
HSUL_12_M	0.378	0.378	0.399	0.378	0.551	0.551	0.582	0.551	0.642	0.642	0.679	0.642	ns
HSUL_12_S	0.378	0.378	0.399	0.378	0.750	0.750	0.799	0.750	0.813	0.813	0.868	0.813	ns
LVCMOS12_F_2	0.512	0.512	0.555	0.512	0.672	0.672	0.692	0.672	0.898	0.898	0.922	0.898	ns
LVCMOS12_F_4	0.512	0.512	0.555	0.512	0.504	0.504	0.521	0.504	0.664	0.664	0.693	0.664	ns
LVCMOS12_F_6	0.512	0.512	0.555	0.512	0.485	0.485	0.507	0.485	0.634	0.634	0.669	0.634	ns
LVCMOS12_F_8	0.512	0.512	0.555	0.512	0.465	0.465	0.489	0.465	0.611	0.611	0.666	0.611	ns
LVCMOS12_M_2	0.512	0.512	0.555	0.512	0.708	0.708	0.727	0.708	0.916	0.916	0.945	0.916	ns
LVCMOS12_M_4	0.512	0.512	0.555	0.512	0.550	0.550	0.573	0.550	0.664	0.664	0.690	0.664	ns
LVCMOS12_M_6	0.512	0.512	0.555	0.512	0.527	0.527	0.554	0.527	0.622	0.622	0.652	0.622	ns
LVCMOS12_M_8	0.512	0.512	0.555	0.512	0.540	0.540	0.571	0.540	0.614	0.614	0.649	0.614	ns
LVCMOS12_S_2	0.512	0.512	0.555	0.512	0.767	0.767	0.803	0.767	0.990	0.990	1.024	0.990	ns
LVCMOS12_S_4	0.512	0.512	0.555	0.512	0.666	0.666	0.704	0.666	0.803	0.803	0.848	0.803	ns
LVCMOS12_S_6	0.512	0.512	0.555	0.512	0.657	0.657	0.695	0.657	0.732	0.732	0.774	0.732	ns
LVCMOS12_S_8	0.512	0.512	0.555	0.512	0.708	0.708	0.761	0.708	0.745	0.745	0.790	0.745	ns
LVCMOS15_F_12	0.414	0.414	0.445	0.414	0.500	0.500	0.522	0.500	0.647	0.647	0.682	0.647	ns
LVCMOS15_F_2	0.414	0.414	0.445	0.414	0.702	0.702	0.722	0.702	0.919	0.919	0.940	0.919	ns
LVCMOS15_F_4	0.414	0.414	0.445	0.414	0.579	0.579	0.601	0.579	0.755	0.755	0.781	0.755	ns
LVCMOS15_F_6	0.414	0.414	0.445	0.414	0.547	0.547	0.569	0.547	0.711	0.711	0.742	0.711	ns

Table 24: **IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$				$T_{OUTBUF\_DELAY\_O\_PAD}$				$T_{OUTBUF\_DELAY\_TD\_PAD}$				Units
	0.90V	0.85V		0.72V	0.90V	0.85V		0.72V	0.90V	0.85V		0.72V	
	-3	-2	-1	-2	-3	-2	-1	-2	-3	-2	-1	-2	
LVCMOS15_F_8	0.414	0.414	0.445	0.414	0.518	0.518	0.538	0.518	0.686	0.686	0.703	0.686	ns
LVCMOS15_M_12	0.414	0.414	0.445	0.414	0.607	0.607	0.644	0.607	0.637	0.637	0.676	0.637	ns
LVCMOS15_M_2	0.414	0.414	0.445	0.414	0.741	0.741	0.770	0.741	0.938	0.938	0.962	0.938	ns
LVCMOS15_M_4	0.414	0.414	0.445	0.414	0.625	0.625	0.651	0.625	0.754	0.754	0.786	0.754	ns
LVCMOS15_M_6	0.414	0.414	0.445	0.414	0.576	0.576	0.604	0.576	0.674	0.674	0.710	0.674	ns
LVCMOS15_M_8	0.414	0.414	0.445	0.414	0.568	0.568	0.601	0.568	0.639	0.639	0.681	0.639	ns
LVCMOS15_S_12	0.414	0.414	0.445	0.414	0.788	0.788	0.855	0.788	0.695	0.695	0.733	0.695	ns
LVCMOS15_S_2	0.414	0.414	0.445	0.414	0.829	0.829	0.864	0.829	1.039	1.039	1.079	1.039	ns
LVCMOS15_S_4	0.414	0.414	0.445	0.414	0.687	0.687	0.725	0.687	0.813	0.813	0.851	0.813	ns
LVCMOS15_S_6	0.414	0.414	0.445	0.414	0.671	0.671	0.710	0.671	0.726	0.726	0.763	0.726	ns
LVCMOS15_S_8	0.414	0.414	0.445	0.414	0.704	0.704	0.755	0.704	0.721	0.721	0.758	0.721	ns
LVCMOS18_F_12	0.418	0.418	0.445	0.418	0.573	0.573	0.601	0.573	0.731	0.731	0.769	0.731	ns
LVCMOS18_F_2	0.418	0.418	0.445	0.418	0.739	0.739	0.760	0.739	0.945	0.945	0.971	0.945	ns
LVCMOS18_F_4	0.418	0.418	0.445	0.418	0.609	0.609	0.630	0.609	0.778	0.778	0.802	0.778	ns
LVCMOS18_F_6	0.418	0.418	0.445	0.418	0.603	0.603	0.633	0.603	0.781	0.781	0.808	0.781	ns
LVCMOS18_F_8	0.418	0.418	0.445	0.418	0.573	0.573	0.600	0.573	0.733	0.733	0.767	0.733	ns
LVCMOS18_M_12	0.418	0.418	0.445	0.418	0.640	0.640	0.678	0.640	0.670	0.670	0.709	0.670	ns
LVCMOS18_M_2	0.418	0.418	0.445	0.418	0.798	0.798	0.822	0.798	0.991	0.991	1.016	0.991	ns
LVCMOS18_M_4	0.418	0.418	0.445	0.418	0.664	0.664	0.693	0.664	0.798	0.798	0.836	0.798	ns
LVCMOS18_M_6	0.418	0.418	0.445	0.418	0.629	0.629	0.663	0.629	0.735	0.735	0.775	0.735	ns
LVCMOS18_M_8	0.418	0.418	0.445	0.418	0.626	0.626	0.661	0.626	0.705	0.705	0.746	0.705	ns
LVCMOS18_S_12	0.418	0.418	0.445	0.418	0.795	0.795	0.861	0.795	0.683	0.683	0.721	0.683	ns
LVCMOS18_S_2	0.418	0.418	0.445	0.418	0.862	0.862	0.897	0.862	1.076	1.076	1.098	1.076	ns
LVCMOS18_S_4	0.418	0.418	0.445	0.418	0.716	0.716	0.758	0.716	0.829	0.829	0.872	0.829	ns
LVCMOS18_S_6	0.418	0.418	0.445	0.418	0.682	0.682	0.724	0.682	0.724	0.724	0.762	0.724	ns
LVCMOS18_S_8	0.418	0.418	0.445	0.418	0.707	0.707	0.760	0.707	0.709	0.709	0.745	0.709	ns
LVDCI_15_F	0.425	0.425	0.462	0.425	0.426	0.426	0.443	0.426	0.548	0.548	0.581	0.548	ns
LVDCI_15_M	0.425	0.425	0.462	0.425	0.553	0.553	0.582	0.553	0.645	0.645	0.685	0.645	ns
LVDCI_15_S	0.425	0.425	0.462	0.425	0.749	0.749	0.803	0.749	0.821	0.821	0.890	0.821	ns
LVDCI_18_F	0.414	0.414	0.447	0.414	0.441	0.441	0.459	0.441	0.560	0.560	0.589	0.560	ns
LVDCI_18_M	0.414	0.414	0.447	0.414	0.554	0.554	0.585	0.554	0.644	0.644	0.683	0.644	ns
LVDCI_18_S	0.414	0.414	0.447	0.414	0.760	0.760	0.818	0.760	0.837	0.837	0.899	0.837	ns
LVDS	0.539	0.539	0.620	0.539	0.626	0.626	0.662	0.626	960.447	960.447	960.447	960.447	ns
MIPI_DPHY_DCI_HS	0.386	0.386	0.415	0.386	0.502	0.502	0.522	0.502	N/A	N/A	N/A	N/A	ns
MIPI_DPHY_DCI_LP	8.438	8.438	8.792	8.438	0.914	0.914	0.937	0.914	N/A	N/A	N/A	N/A	ns
POD10_DCI_F	0.408	0.408	0.430	0.408	0.425	0.425	0.444	0.425	0.555	0.555	0.584	0.555	ns
POD10_DCI_M	0.408	0.408	0.430	0.408	0.542	0.542	0.571	0.542	0.640	0.640	0.681	0.640	ns
POD10_DCI_S	0.408	0.408	0.430	0.408	0.754	0.754	0.815	0.754	0.850	0.850	0.917	0.850	ns
POD10_F	0.407	0.407	0.430	0.407	0.438	0.438	0.459	0.438	0.569	0.569	0.601	0.569	ns
POD10_M	0.407	0.407	0.430	0.407	0.538	0.538	0.568	0.538	0.630	0.630	0.667	0.630	ns
POD10_S	0.407	0.407	0.430	0.407	0.766	0.766	0.821	0.766	0.836	0.836	0.894	0.836	ns

Table 24: **IOB High Performance (HP) Switching Characteristics *(Cont'd)***

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$				$T_{OUTBUF\_DELAY\_O\_PAD}$				$T_{OUTBUF\_DELAY\_TD\_PAD}$				Units
	0.90V	0.85V		0.72V	0.90V	0.85V		0.72V	0.90V	0.85V		0.72V	
	-3	-2	-1	-2	-3	-2	-1	-2	-3	-2	-1	-2	
POD12_DCI_F	0.409	0.409	0.431	0.409	0.425	0.425	0.443	0.425	0.558	0.558	0.586	0.558	ns
POD12_DCI_M	0.409	0.409	0.431	0.409	0.543	0.543	0.572	0.543	0.638	0.638	0.678	0.638	ns
POD12_DCI_S	0.409	0.409	0.431	0.409	0.772	0.772	0.822	0.772	0.862	0.862	0.929	0.862	ns
POD12_F	0.409	0.409	0.431	0.409	0.455	0.455	0.476	0.455	0.595	0.595	0.626	0.595	ns
POD12_M	0.409	0.409	0.431	0.409	0.551	0.551	0.582	0.551	0.641	0.641	0.679	0.641	ns
POD12_S	0.409	0.409	0.431	0.409	0.767	0.767	0.817	0.767	0.832	0.832	0.889	0.832	ns
SLVS_400_18	0.539	0.539	0.620	0.539	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	ns
SSTL12_DCI_F	0.381	0.381	0.399	0.381	0.425	0.425	0.443	0.425	0.558	0.558	0.586	0.558	ns
SSTL12_DCI_M	0.381	0.381	0.399	0.381	0.557	0.557	0.587	0.557	0.654	0.654	0.694	0.654	ns
SSTL12_DCI_S	0.381	0.381	0.399	0.381	0.754	0.754	0.803	0.754	0.842	0.842	0.908	0.842	ns
SSTL12_F	0.403	0.403	0.403	0.403	0.412	0.412	0.430	0.412	0.538	0.538	0.566	0.538	ns
SSTL12_M	0.403	0.403	0.403	0.403	0.553	0.553	0.584	0.553	0.641	0.641	0.676	0.641	ns
SSTL12_S	0.403	0.403	0.403	0.403	0.758	0.758	0.808	0.758	0.823	0.823	0.879	0.823	ns
SSTL135_DCI_F	0.366	0.366	0.399	0.366	0.411	0.411	0.428	0.411	0.537	0.537	0.565	0.537	ns
SSTL135_DCI_M	0.366	0.366	0.399	0.366	0.551	0.551	0.582	0.551	0.645	0.645	0.685	0.645	ns
SSTL135_DCI_S	0.366	0.366	0.399	0.366	0.746	0.746	0.799	0.746	0.829	0.829	0.893	0.829	ns
SSTL135_F	0.378	0.378	0.399	0.378	0.408	0.408	0.428	0.408	0.528	0.528	0.561	0.528	ns
SSTL135_M	0.378	0.378	0.399	0.378	0.555	0.555	0.585	0.555	0.641	0.641	0.679	0.641	ns
SSTL135_S	0.378	0.378	0.399	0.378	0.772	0.772	0.823	0.772	0.827	0.827	0.878	0.827	ns
SSTL15_DCI_F	0.402	0.402	0.417	0.402	0.412	0.412	0.429	0.412	0.531	0.531	0.563	0.531	ns
SSTL15_DCI_M	0.402	0.402	0.417	0.402	0.553	0.553	0.583	0.553	0.645	0.645	0.685	0.645	ns
SSTL15_DCI_S	0.402	0.402	0.417	0.402	0.768	0.768	0.822	0.768	0.847	0.847	0.912	0.847	ns
SSTL15_F	0.371	0.371	0.400	0.371	0.408	0.408	0.428	0.408	0.530	0.530	0.556	0.530	ns
SSTL15_M	0.371	0.371	0.400	0.371	0.554	0.554	0.585	0.554	0.639	0.639	0.677	0.639	ns
SSTL15_S	0.371	0.371	0.400	0.371	0.767	0.767	0.817	0.767	0.813	0.813	0.867	0.813	ns
SSTL18_I_DCI_F	0.329	0.329	0.336	0.329	0.445	0.445	0.461	0.445	0.566	0.566	0.595	0.566	ns
SSTL18_I_DCI_M	0.329	0.329	0.336	0.329	0.554	0.554	0.585	0.554	0.644	0.644	0.683	0.644	ns
SSTL18_I_DCI_S	0.329	0.329	0.336	0.329	0.762	0.762	0.818	0.762	0.837	0.837	0.899	0.837	ns
SSTL18_I_F	0.316	0.316	0.337	0.316	0.454	0.454	0.476	0.454	0.578	0.578	0.608	0.578	ns
SSTL18_I_M	0.316	0.316	0.337	0.316	0.571	0.571	0.603	0.571	0.652	0.652	0.692	0.652	ns
SSTL18_I_S	0.316	0.316	0.337	0.316	0.782	0.782	0.835	0.782	0.816	0.816	0.870	0.816	ns
SUB_LVDS	0.539	0.539	0.620	0.539	0.660	0.660	0.692	0.660	969.863	969.863	969.863	969.863	ns

IOB 3-state Output Switching Characteristics

Table 25 specifies the values of $T_{OUTBUF\_DELAY\_TE\_PAD}$ and $T_{INBUF\_DELAY\_IBUFDIS\_O}$. $T_{OUTBUF\_DELAY\_TE\_PAD}$ is the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{INBUF\_DELAY\_IBUFDIS\_O}$ is the IOB delay from IBUFDISABLE to O output. In HP I/O banks, the internal DCI termination turn-off time is always faster than $T_{OUTBUF\_DELAY\_TE\_PAD}$ when the DCITERMDISABLE pin is used.

Table 25: **IOB 3-state Output Switching Characteristics**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages				Units
		0.90V	0.85V		0.72V	
		-3	-2	-1	-2	
$T_{OUTBUF\_DELAY\_TE\_PAD}$	T input to pad high-impedance for the I/O banks	5.330	5.330	5.341	5.330	ns
$T_{INBUF\_DELAY\_IBUFDIS\_O}$	IBUF turn-on time from IBUFDISABLE to O output for the I/O banks	0.936	0.936	1.037	0.936	ns

Input Delay Measurement Methodology

Table 26 shows the test setup parameters used for measuring input delay.

Table 26: **Input Delay Measurement Methodology**

Description	I/O Standard Attribute	V_L (1)(2)	V_H (1)(2)	V_{MEAS} (1)(4)(6)	V_{REF} (1)(3)(5)
LVCMOS, 1.2V	LVCMOS12	0.1	1.1	0.6	–
LVCMOS, LVDCI, HSLVDCI, 1.5V	LVCMOS15, LVDCI_15, HSLVDCI_15	0.1	1.4	0.75	–
LVCMOS, LVDCI, HSLVDCI, 1.8V	LVCMOS18, LVDCI_18, HSLVDCI_18	0.1	1.7	0.9	–
HSTL (high-speed transceiver logic), class I, 1.2V	HSTL_I_12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
HSTL, class I, 1.5V	HSTL_I	V_{REF} – 0.325	V_{REF} + 0.325	V_{REF}	0.75
HSTL, class I, 1.8V	HSTL_I_18	V_{REF} – 0.4	V_{REF} + 0.4	V_{REF}	0.9
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
SSTL12 (stub series terminated logic), 1.2V	SSTL12	V_{REF} – 0.25	V_{REF} + 0.25	V_{REF}	0.6
SSTL135 and SSTL135 class II, 1.35V	SSTL135, SSTL135_II	V_{REF} – 0.2875	V_{REF} + 0.2875	V_{REF}	0.675
SSTL15 and SSTL15 class II, 1.5V	SSTL15, SSTL15_II	V_{REF} – 0.325	V_{REF} + 0.325	V_{REF}	0.75
SSTL18, class I and II, 1.8V	SSTL18_I, SSTL18_II	V_{REF} – 0.4	V_{REF} + 0.4	V_{REF}	0.9
POD10, 1.0V	POD10	V_{REF} – 0.2	V_{REF} + 0.2	V_{REF}	0.7
POD12, 1.2V	POD12	V_{REF} – 0.24	V_{REF} + 0.24	V_{REF}	0.84
DIFF_HSTL, class I, 1.2V	DIFF_HSTL_I_12	0.6 – 0.25	0.6 + 0.25	0 (6)	–
DIFF_HSTL, class I, 1.5V	DIFF_HSTL_I	0.75 – 0.325	0.75 + 0.325	0 (6)	–
DIFF_HSTL, class I, 1.8V	DIFF_HSTL_I_18	0.9 – 0.4	0.9 + 0.4	0 (6)	–

Table 26: **Input Delay Measurement Methodology *(Cont'd)***

Description	I/O Standard Attribute	V_L (1)(2)	V_H (1)(2)	V_{MEAS} (1)(4)(6)	V_{REF} (1)(3)(5)
DIFF_HSUL, 1.2V	DIFF_HSUL_12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_SSTL, 1.2V	DIFF_SSTL12	0.6 – 0.25	0.6 + 0.25	0(6)	–
DIFF_SSTL135 and DIFF_SSTL135 class II, 1.35V	DIFF_SSTL135, DIFF_SSTL135_II	0.675 – 0.2875	0.675 + 0.2875	0(6)	–
DIFF_SSTL15 and DIFF_SSTL15 class II, 1.5V	DIFF_SSTL15, DIFF_SSTL15_II	0.75 – 0.325	0.75 + 0.325	0(6)	–
DIFF_SSTL18_I, DIFF_SSTL18_II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	0.9 – 0.4	0.9 + 0.4	0(6)	–
DIFF_POD10, 1.0V	DIFF_POD10	0.5 – 0.2	0.5 + 0.2	0(6)	–
DIFF_POD12, 1.2V	DIFF_POD12	0.6 – 0.25	0.6 + 0.25	0(6)	–
LVDS (low-voltage differential signaling), 1.8V	LVDS	0.9 – 0.125	0.9 + 0.125	0(6)	–
SUB_LVDS, 1.8V	SUB_LVDS	0.9 – 0.125	0.9 + 0.125	0(6)	–
SLVS, 1.8V	SLVS_400_18	0.9 – 0.125	0.9 + 0.125	0(6)	–
MIPI D-PHY (high speed) 1.2V	MIPI_DPHY_DCI_HS	0.2 – 0.125	0.2 + 0.125	0(6)	–
MIPI D-PHY (low power) 1.2V	MIPI_DPHY_DCI_LP	0.715 – 0.2	0.715 + 0.2	0(6)	–

Notes:

1. The input delay measurement methodology parameters for LVDCI/HSLVDCI are the same for LVCMOS standards of the same voltage. Parameters for all other DCI standards are the same for the corresponding non-DCI standards.
2. Input waveform switches between V_L and V_H.
3. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst case of these measurements. V_{REF} values listed are typical.
4. Input voltage level from which measurement starts.
5. This is an input voltage reference that bears no relation to the V_{REF}/V_{MEAS} parameters found in IBIS models and/or noted in Figure 1.
6. The value given is the differential input voltage.

Output Delay Measurement Methodology

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in Figure 1 and Figure 2.

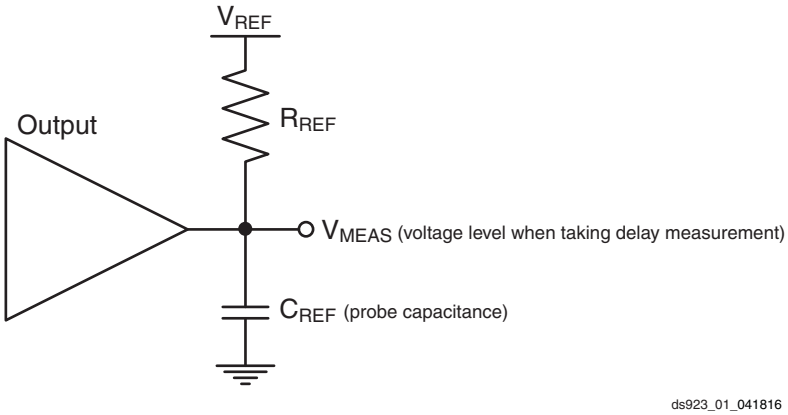

Figure 1: **Single-Ended Test Setup**

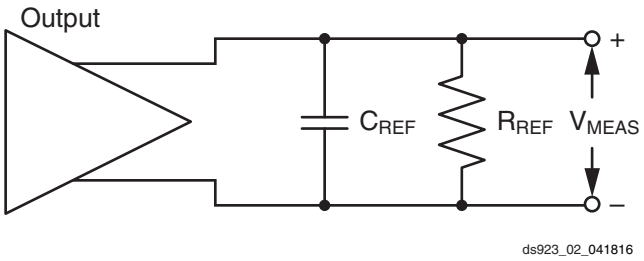

Figure 2: **Differential Test Setup**

Parameters V_{REF}, R_{REF}, C_{REF}, and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from Table 27.
2. Record the time to V_{MEAS}.
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS}.
5. Compare the results of step 2 and step 4. The increase or decrease in delay yields the actual propagation delay of the PCB trace.